PBSS4240X

40 V, 2 A NPN low VCEsat (BISS) transistor

15 October 2012

Product data sheet

1. Product profile

1.1 General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a medium power and flat lead SOT89 Surface-Mounted Device (SMD) plastic package. PNP complement: PBSS5240X.

1.2 Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- · High efficiency due to less heat generation

1.3 Applications

- DC-to-DC conversion
- Supply line switching
- Battery charger
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)
- Inductive load driver (e.g. relays, buzzers and motors)

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	40	V
I _C	collector current		-	-	2	Α
I _{CM}	peak collector current		-	-	3	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	260	mΩ
I _{CRM}	repetitive peak collector current	$t_p \le 20 \text{ ms}; \delta \le 0.33 \; ; \text{pulsed}$	-	-	2.5	Α



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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		C
2	С	collector		В
3	В	base	3 2 1	- N
			SOT89	sym123

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS4240X	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89		

4. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4240X	S47

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	40	V
V _{CEO}	collector-emitter voltage	open base		-	40	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current			-	2	Α
I _{CRM}	repetitive peak collector current	$\delta \le 0.33$; $t_p \le 20$ ms; pulsed		-	2.5	Α
I _{CM}	peak collector current			-	3	Α
I _B	base current			-	300	mA
I _{BM}	peak base current			-	1	Α
P _{tot}	total power dissipation		[1]	-	0.5	W
			[2]	-	0.95	W

PBSS4240X

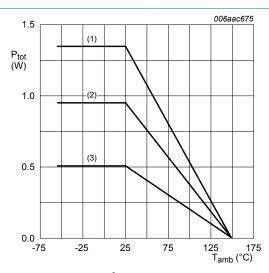
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Symbol	Parameter	Conditions		Min	Max	Unit
			[3]	-	1.35	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



- (1) FR4 PCB, mounting pad for collector 6 cm²
- (2) FR4 PCB, mounting pad for collector 1 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	unction to nt	[1]	-	-	250	K/W
from junction to ambient			[2]	-	-	132	K/W
	ambient		[3]	-	-	93	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	16	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

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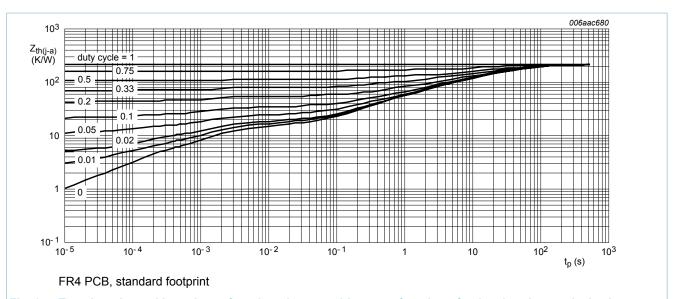


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

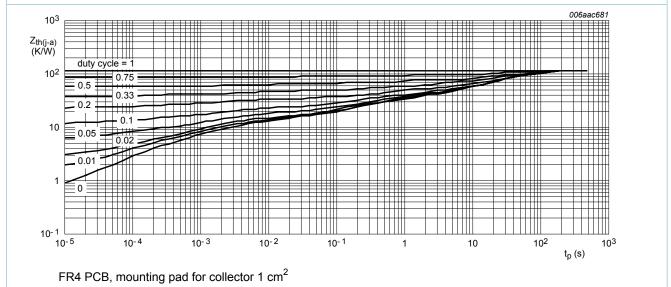
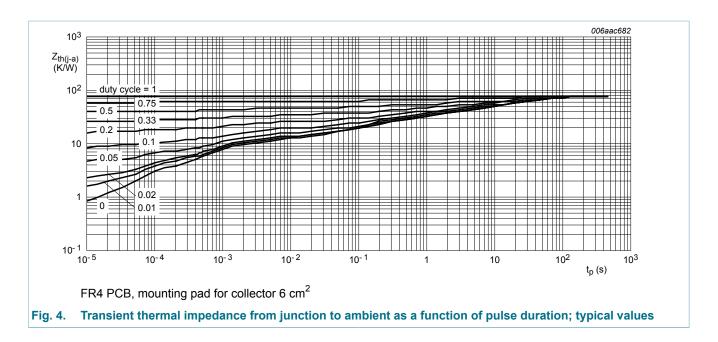


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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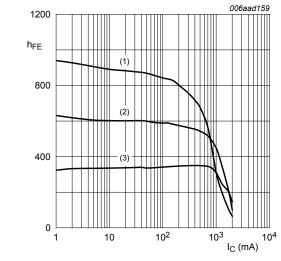
7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 40 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 40 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{CEO}	collector-emitter cut-off current	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 1 mA; T _{amb} = 25 °C	300	-	-	
		V _{CE} = 5 V; I _C = 500 mA; T _{amb} = 25 °C	300	-	900	
		V _{CE} = 5 V; I _C = 1 A; T _{amb} = 25 °C	200	-	-	
		V_{CE} = 5 V; I_{C} = 2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	75	-	-	
V _{CEsat}	collector-emitter	I _C = 100 mA; I _B = 1 mA; T _{amb} = 25 °C	-	-	80	mV
	saturation voltage	I _C = 500 mA; I _B = 50 mA; T _{amb} = 25 °C	-	-	140	mV
		I_{C} = 1 A; I_{B} = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb}$ = 25 °C	-	-	260	mV
		I_{C} = 2 A; I_{B} = 200 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb}$ = 25 °C	-	-	510	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = 1 A; I_{B} = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-	260	mΩ

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{BEsat}	base-emitter saturation voltage	I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	1.2	V
V _{BEon}	base-emitter turn-on voltage	V_{CE} = 5 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-	1.1	V
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 50 mA; f = 100 MHz; T_{amb} = 25 °C	150	-	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_{E} = 0 \text{ A}; i_{e} = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	10	pF



 $V_{CE} = 5 V$

(1) T_{amb} = 150 °C

(2) T_{amb} = 25 °C

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 5. DC current gain as a function of collector current; typical values

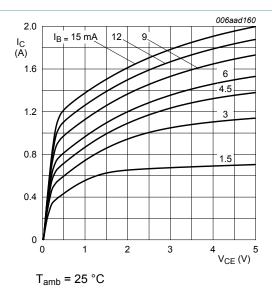
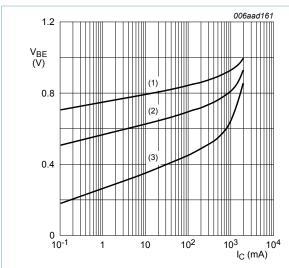


Fig. 6. Collector current as a function of collectoremitter voltage; typical values

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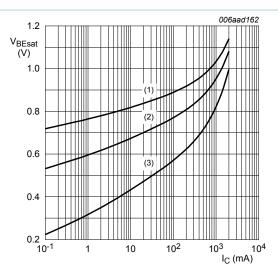
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 7. Base-emitter voltage as a function of collector current; typical values



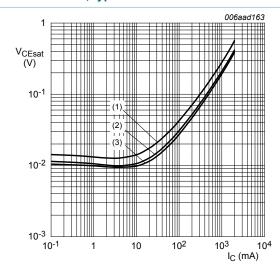
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

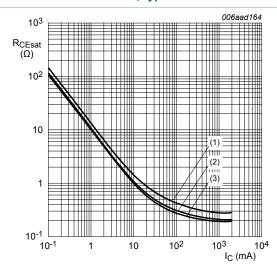


$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(3)
$$T_{amb}$$
= -55 °C

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

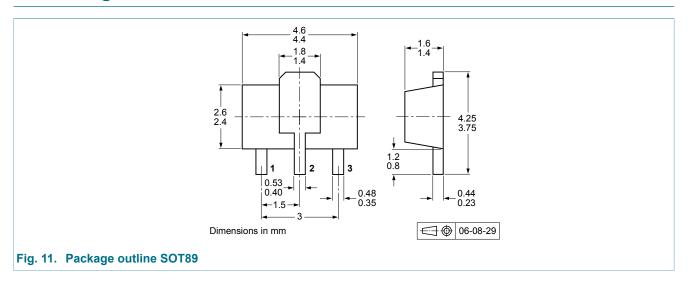
(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

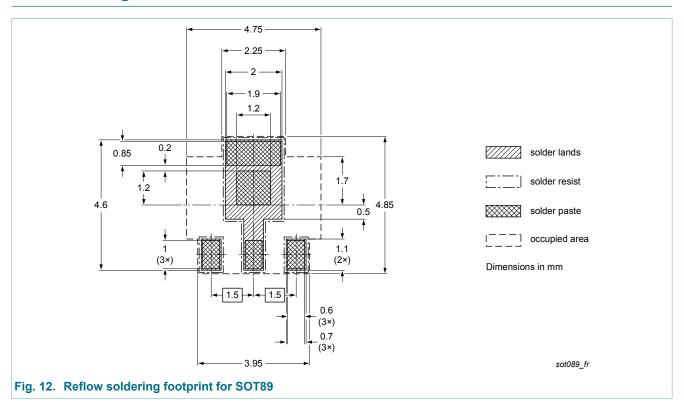
Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

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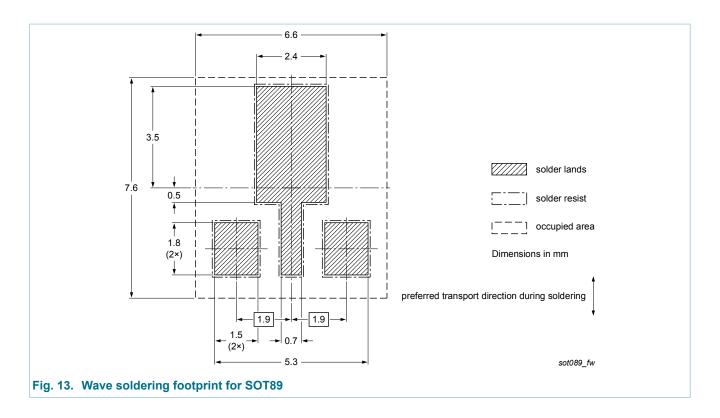
8. Package outline



9. Soldering



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10. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4240X v.1	20121015	Product data sheet	-	-

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